IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Amended) A method [for] of using Si-Ge-C in selective etch applications [in conjunction with a silicon substrate], comprising:

growing one or more epitaxial layers [sequentially, starting at the silicon substrate, wherein at least one of the epitaxial layers comprises Si-Ge-C, wherein the carbon of the Si-Ge-C layer is about 4.5 atomic percent] on a single crystal silicon substrate, at least one of which is a Si-Ge-C layer, wherein the carbon of the Si-Ge-C layer is an amount sufficient to exhibit etch selectivity with respect to the single crystal silicon substrate and/or one or more of the epitaxial layers adjacent the SI-Ge-C layer; and

[selectively etching the one or more layers adjacent to the Si-Ge-C layer and/or the Si-Ge-C layer wherein the selective etching includes applying a KOH etchant to the Si-Ge-C layer] etching the Si-Ge-C layer, and the single crystal silicon substrate and/or one or more of the epitaxial layers adjacent the Si-Ge-C layer.

Please add claims 2-20 as follows:

49. 2. The method of claim 1, wherein the Si-Ge-C layer etches slower than the one or more adjacent epitaxial layers.

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50. 3. The method of claim 1, wherein the Si-Ge-C layer etches slower than the single crystal silicon substrate.

51. 4. The method of claim 1, wherein the Si-Ge-C layer etches faster than the one or more adjacent epitaxial layers.

52. 5. The method of claim 1, wherein the Si-Ge-C layer etches faster than the single crystal silicon substrate.

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8. The method of claim 1, wherein the etching includes applying an etchant selected from the group of KOH and HNA.

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11. A method of using Si-Ge-C in selective etch applications in conjunction with a single crystal substrate, comprising:

growing one or more epitaxial layers sequentially, starting at the single crystal substrate surface, wherein at least one of the epitaxial layers comprises Si-Ge-C, wherein the carbon of the Si-Ge-C layer is up to 5 atomic percent; and

etching the Si-Ge-C layer, and the single crystal substrate and/or one or more of the epitaxial layers adjacent the Si-Ge-C layer.

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8. The method of claim 11, wherein the Si-Ge-C layer etches slower than the one or more adjacent epitaxial layers.

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9. The method of claim 11, wherein the Si-Ge-C layer etches slower than the single crystal substrate.

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10. The method of claim 11, wherein the Si-Ge-C layer etches faster than the one or more adjacent epitaxial layers.

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11. The method of claim 11, wherein the Si-Ge-C layer etches faster than the single crystal substrate.

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12. The method of claim 11, 8, 9, 10, or 11, wherein the single crystal substrate is a material selected from the group of silicon, silicon-germanium, and germanium.

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13. The method of claim 11, wherein the etching includes applying an etchant selected from the group of KOH and HNA.

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14. A method of using Si-Ge-C in selective etch applications in conjunction with a substrate, comprising:

growing one or more layers sequentially, starting at the substrate, wherein at least one of the layers comprises Si-Ge-C, wherein the carbon of the Si-Ge-C layer is up to 10 atomic percent, and

etching the Si-Ge-C layer and one or more layers adjacent to the Si-Ge-C layer and/or the substrate.

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15. The method of claim 14, wherein the Si-Ge-C layer etches slower than the one or more adjacent layers.

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16. The method of claim 14, wherein the Si-Ge-C layer etches slower than the substrate.

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17. The method of claim 14, wherein the Si-Ge-C layer etches faster than the one or more adjacent layers.

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18. The method of claim 14, wherein the Si-Ge-C layer etches faster than the substrate.

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19. The method of claim 14, 15, 16, 17, or 18, wherein the substrate is a material selected from the group of silicon, silicon-germanium, and germanium.

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20. The method of claim 14, wherein the etching includes applying an etchant selected from the group of KOH and HNA.--

Please enter claim 1 in clean form as follows:

1. A method of using Si-Ge-C in selective etch applications, comprising:

growing one or more epitaxial layers on a single crystal silicon substrate, at least one of which is a Si-Ge-C layer, wherein the carbon of the Si-Ge-C layer is an amount sufficient to exhibit etch selectivity with respect to the single crystal silicon substrate and/or one or more of the epitaxial layers adjacent to the Si-Ge-C layer; and

etching the Si-Ge-C layer, and the single crystal silicon substrate and/or one or more of the epitaxial layers adjacent to the Si-Ge-C layer.